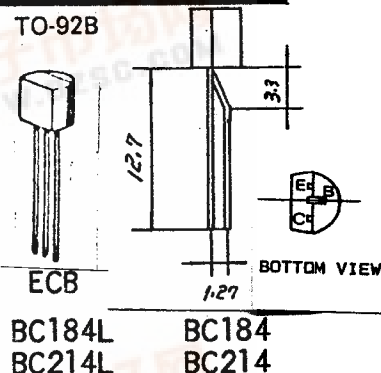




BC183, L · BC213, L

COMPLEMENTARY SILICON AF SMALL SIGNAL AMPLIFIERS & DRIVERS

The BC183, BC183L (NPN) & BC213, BC213L (PNP) are complementary silicon planar epitaxial transistors for use in AF small signal amplifiers and drivers, as well as for low power universal applications. Both types feature good linearity of D.C. current gain.



ABSOLUTE MAXIMUM RATINGS

	BC183, L	BC213, L
Collector-Base Voltage	V_{CB0} 45V	45V
Collector-Emitter Voltage	V_{CE0} 30V	30V
Emitter-Base Voltage	V_{EB0} 6V	5V
Collector Current	I_C	200mA
Total Power Dissipation @ $T_A=25^{\circ}C$ Derate above $25^{\circ}C$	P_{tot}	300mW 2.4mW/ $^{\circ}C$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55 to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}C$)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV_{CE0}	30			V	$I_C=2mA$ $I_B=0$
Collector-Base Breakdown Voltage	BV_{CB0}	45			V	$I_C=10\mu A$ $I_E=0$
Emitter-Base Breakdown Voltage BC183, L BC213, L	BV_{EB0}	6 5			V	$I_E=10\mu A$ $I_C=0$
Collector Cutoff Current	I_{CB0}			15	nA	$V_{CB}=30V$ $I_E=0$
Emitter Cutoff Current	I_{EB0}			15	nA	$V_{EB}=4V$ $I_C=0$



ELECTRICAL CHARACTERISTICS (TA=25°C)

Collector-Emitter Saturation BC183,L BC213,L	V _{CE(sat)}	0.07	0.25 0.6	V	I _C =10mA I _B =0.5mA I _C =100mA I _B =5mA*
Base-Emitter Saturation BC183,L BC213,L	V _{BE(sat)}		1.2 1.1	V	I _C =100mA I _B =5mA*
Base-Emitter Voltage BC183,L BC213,L	V _{BE}	0.55 0.6	0.7 0.72	V	V _{CE} =5V I _C =2mA
D.C. Current Gain BC183,L BC213,L BC183,L BC213,L	H _{FE}	100 220 140 130	120		V _{CE} =5V I _C =10μA V _{CE} =5V I _C =2mA V _{CE} =5V I _C =100mA*
Small Signal Current Gain (f=1KHz) BC183,L BC213,L Group A Group B Group C	h _{fe}	240 140 125 240 450	900 260 500 900		V _{CE} =5V I _C =2mA
Output Capacitance BC183,L BC213,L	C _{ob}	3 5	5	pF	V _{CB} =10V I _E =0 f=1MHz
Input Capacitance BC183,L	C _{ib}	9.5		pF	V _{EB} =0.5V I _E =0 f=1MHz
Current Gain-Bandwidth Product BC183,L BC213,L	f _T	280 350		MHz	I _C =10mA V _{CE} =5V f=100MHz
Noise Figure BC183,L BC213,L	NF		10	dB	I _C =200μA V _{CE} =5V R _G =2KΩ NB=15.7KHz f ₁ =10Hz f ₂ =10KHz

* Pulse Test : Pulse Width = 300μS, Duty Cycle ≤ 2%.